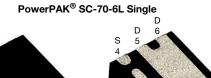
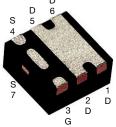


Vishay Siliconix

N-Channel 30 V (D-S) MOSFET







Bottom View

Marking Code: AS

PRODUCT SUMMARY									
V _{DS} (V)	30								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10 \text{ V}$	0.018								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 6 \text{ V}$	0.020								
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5 \text{ V}$	0.022								
Q _g typ. (nC)	5								
I _D (A) ^a	12								
Configuration	Single								

FEATURES

- TrenchFET® power MOSFET
- 100 % R_g tested

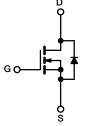




RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

- DC/DC converters and synchronous buck converters
 - Lower ringing voltage from soft turn-on
 - High efficiency from fast turn-off
 - Lower shoot-through possibility



N-Channel MOSFE	EΤ	Γ
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ORDERING INFORMATION					
Package	PowerPAK SC-70				
Lead (Pb)-free and halogen-free	SiA462DJ-T1-GE3				

ABSOLUTE MAXIMUM RATINGS (20 O, arriodo					
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V_{DS}	30	V		
Gate-source voltage		V_{GS}	± 20			
	T _C = 25 °C		12 ^a			
Continuous drain current (T _J = 150 °C)	T _C = 70 °C		12 ^a			
	T _A = 25 °C	I _D	12 ^{a, b, c}			
	T _A = 70 °C		9.7 ^{b, c}	Α		
Pulsed drain current (t = 300 μs)	•	I _{DM}	40			
Continuous source drain diade surrent	T _C = 25 °C		12 ^a			
Continuous source-drain diode current	T _A = 25 °C	l _S —	2.9 b, c			
	T _C = 25 °C		19			
Manifestore and all all additions	T _C = 70 °C		12	14/		
Maximum power dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	─ W		
	T _A = 70 °C		2.2 b, c			
Operating junction and storage temperature ran	T _J , T _{stg}	-55 to +150	00			
Soldering recommendations (peak temperature)	d, e		260	- °C		

THERMAL RESISTANCE RATINGS									
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT					
Maximum junction-to-ambient b, f	t ≤ 5 s	R_{thJA}	28	36	°C ///				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	5.3	6.5	°C/W				

Notes

- Based on package limited
- Surface mounted on 1" x 1" FR4 board
- t = 5 s
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
 e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
 f. Maximum under steady state conditions is 80 °C/W



Vishay Siliconix

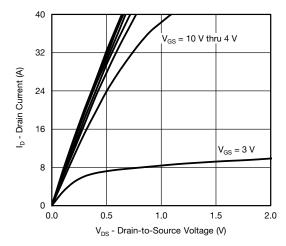
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$		-	34	-	mV/°C
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA	-	-5		
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.2	-	2.4	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
-		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10	-	-	Α
	B(GII)	V _{GS} = 10 V, I _D = 9 A	_	0.015	0.018	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 6 V, I _D = 7 A	_	0.016	0.020	Ω
	1 103(011)	V _{GS} = 4.5 V, I _D = 7 A	_	0.018	0.022	32
Forward transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 9 \text{ A}$	_	35	-	S
Dynamic b	91S	V _{DS} = 10 V, I _D = 071		1 00		
Input capacitance	C _{iss}		T -	570	_	pF
Output capacitance	Coss	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	_	126	_	
Reverse transfer capacitance	C _{rss}	103 10 1, 103 0 1, 1 11111	_	52	_	
Tion of the control o	-155	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 12 A	_	11	17	nC
Total gate charge	Qg	103 10 1, 103 10 1, 10 1211	_	5	7.5	
Gate-source charge	Q _{qs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 12 \text{ A}$	-	1.7	-	
Gate-drain charge	Q _{gd}	20 4 , 40 4 , 5	-	1.6	-	
Gate resistance	R _g	f = 1 MHz	0.2	1	2	Ω
Turn-on delay time	t _{d(on)}		-	5	10	
Rise time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega,$	-	10	20	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	15	30	
Fall time	t _f		-	10	20	
Turn-on delay time	t _{d(on)}		-	12	25	ns
Rise time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 1.5 \Omega,$	-	15	30	
Turn-off delay time	t _{d(off)}	$I_D \cong 10 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$	-	15	30	
Fall time	t _f		-	10	20	
Drain-Source Body Diode Characteristi	cs					·
Continuous source-drain diode current	Is	T _C = 25 °C	-	-	12	
Pulse diode forward current ^a	I _{SM}		-	-	40	A
Body diode voltage	V _{SD}	I _S = 10 A	-	0.85	1.2	V
Body diode reverse recovery time	t _{rr}		-	20	40	ns
Body diode reverse recovery charge	Q _{rr}	$I_F = 10 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	11	20	nC
Reverse recovery fall time	ta	$T_{\rm J} = 25 ^{\circ}{\rm C}$	-	12	-	1
Reverse recovery rise time					-	ns

Notes

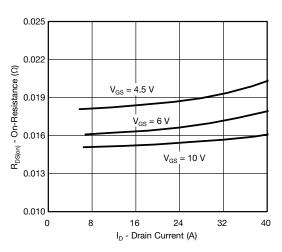
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

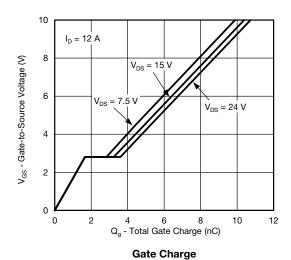


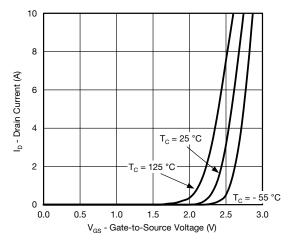


Output Characteristics

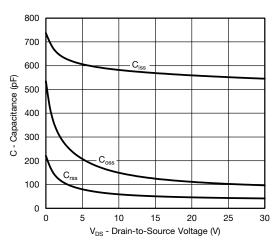


On-Resistance vs. Drain Current and Gate Voltage

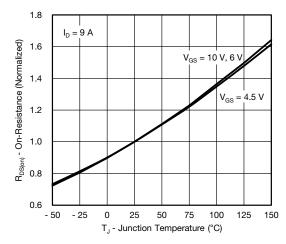




Transfer Characteristics

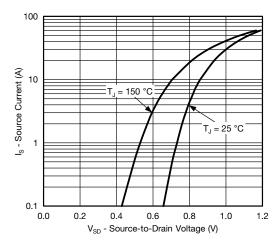


Capacitance

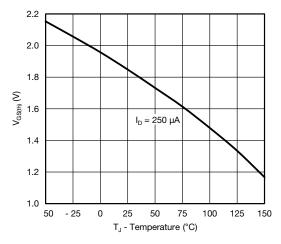


On-Resistance vs. Junction Temperature

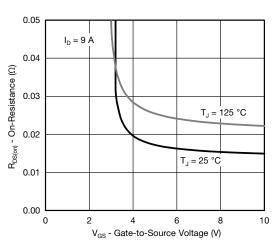




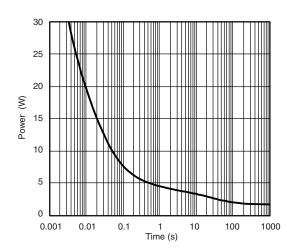
Source-Drain Diode Forward Voltage



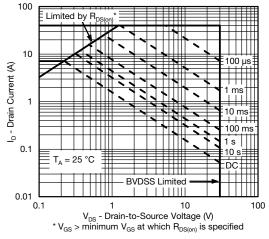
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage

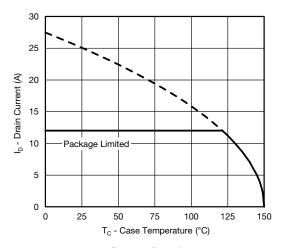


Single Pulse Power, Junction-to-Ambient

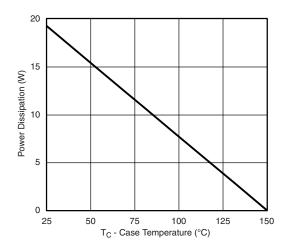


Safe Operating Area, Junction-to-Ambient





Current Derating a

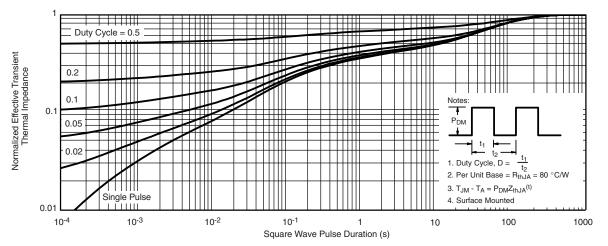


Power, Junction-to-Case

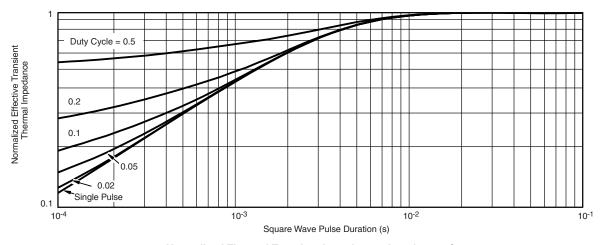
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63269.





Vishay Siliconix

PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD					DUAL PAD							
DIM	M	ILLIMETER	RS	INCHES		MILLIMETERS			INCHES				
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
D1	0.85	0.95	1.05	0.033 0.037 0.041		0.513	0.613	0.713	0.020	0.024	0.028		
D2	0.135	0.235	0.335	0.005 0.009 0.013									
Е	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085	
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041	
E2	0.345	0.395	0.445	0.014	0.016	0.018							
E3	0.425	0.475	0.525	0.017	0.019	0.021							
е		0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP			
K1		0.400 TYP			0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP			0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP					•	•			
K4		0.355 TYP			0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015	
T							0.05	0.10	0.15	0.002	0.004	0.006	

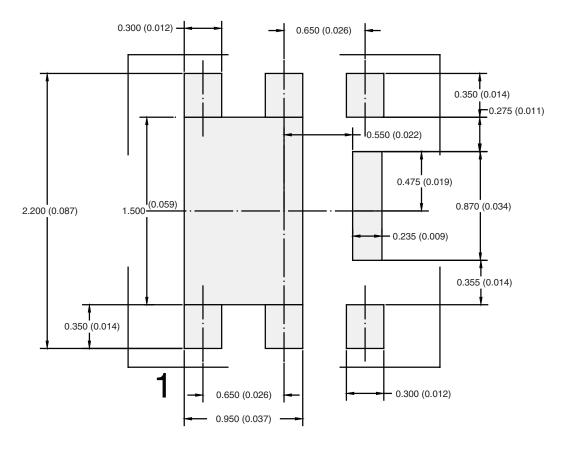
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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Vishay

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